



SHEET 1 OF 1

INFORMATION DISCLOSURE
CITATION IN AN
APPLICATION

(PTO-1449)

ATTY. DOCKET NO.
074968-0011SERIAL NO.
10/812,416APPLICANT
Tetsuzo UEDA, et al.FILING DATE
March 30, 2004GROUP
2811

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes-Number -Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation Yes No

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
SC		NAOTAKA KURODA ET AL., "Step-Controlled VPE Growth of SiC Single Crystals at Low Temperatures", Extended Abstracts of the 19th Conference on Solid State Devices and Materials, Tokyo, 1987, pp. 227-230

EXAMINER
/Sara Crane/DATE CONSIDERED
10/16/2006

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.

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						Yes	No
SC		JP 8-125275	05-17-1996	SANYO ELECTRIC CO. LTD.		Japan (w/ English Abstract)	

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
		N. Kuroda et al., "Step - Controlled VPE Growth of SiC Single Crystals at Low Temperatures" Extended Abstracts of the 19th Conference on Solid State Devices and Materials, Tokyo, 1987, pp. 227-230	

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